ABSTRACT

A polishing-material composition, for polishing of LSI devices, which is a polishing-material composition comprising water and cerium oxide which has been surface-treated with a coupling agent, wherein the maximum value is no greater than 5 μm and the average value is 0.01-1.0 μm in the secondary particle size distribution of the cerium oxide. Also, a polishing method for LSI devices which employs the polishing-material composition.